

BAT54LT1

Preferred Device

Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

- Extremely Fast Switching Speed
- Low Forward Voltage – 0.35 Volts (Typ) @ $I_F = 10 \text{ mA}$
- Pb-Free Package is Available

MAXIMUM RATINGS ($T_J = 125^\circ\text{C}$ unless otherwise noted)

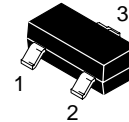
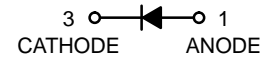
Rating	Symbol	Value	Unit
Reverse Voltage	V_R	30	Volts
Forward Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_F	200 2.0	mW mW/ $^\circ\text{C}$
Forward Current (DC)	I_F	200 Max	mA
Junction Temperature	T_J	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



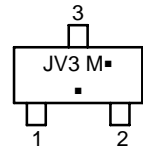
ON Semiconductor®

30 VOLTS SILICON HOT-CARRIER DETECTOR AND SWITCHING DIODES



(TO-236AB)
SOT-23
CASE 318
STYLE 8

MARKING DIAGRAM



JV3 = Device Code
M = Date Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
BAT54LT1	SOT-23	3000/Tape & Reel
BAT54LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

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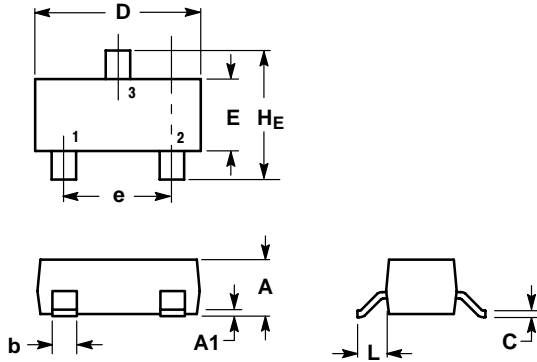
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ($I_R = 10 \mu\text{A}$)	$V_{(BR)R}$	30	–	–	Volts
Total Capacitance ($V_R = 1.0 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_T	–	7.6	10	pF
Reverse Leakage ($V_R = 25 \text{ V}$)	I_R	–	0.5	2.0	μA dc
Forward Voltage ($I_F = 0.1 \text{ mA}$ dc)	V_F	–	0.22	0.24	Vdc
Forward Voltage ($I_F = 30 \text{ mA}$ dc)	V_F	–	0.41	0.5	Vdc
Forward Voltage ($I_F = 100 \text{ mA}$ dc)	V_F	–	0.52	0.8	Vdc
Reverse Recovery Time ($I_F = I_R = 10 \text{ mA}$ dc, $I_{R(REC)} = 1.0 \text{ mA}$ dc, Figure 1)	t_{rr}	–	–	5.0	ns
Forward Voltage ($I_F = 1.0 \text{ mA}$ dc)	V_F	–	0.29	0.32	Vdc
Forward Voltage ($I_F = 10 \text{ mA}$ dc)	V_F	–	0.35	0.40	Vdc
Forward Current (DC)	I_F	–	–	200	mA
Repetitive Peak Forward Current	I_{FRM}	–	–	300	mA
Non-Repetitive Peak Forward Current ($t < 1.0 \text{ s}$)	I_{FSM}	–	–	600	mA

BAT54LT1

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AL



NOTES:

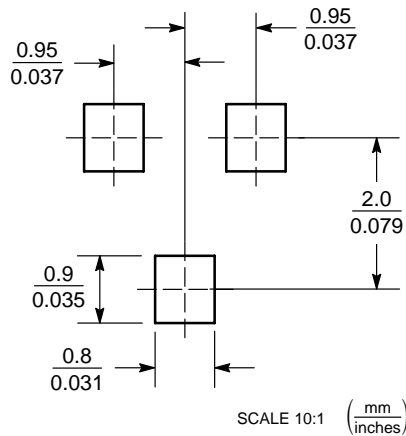
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 8:

- PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

SOLDERING FOOTPRINT*



SCALE 10:1 ($\frac{\text{mm}}{\text{inches}}$)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.